

<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  <b>(PTO-1449)</b>			<b>ATTY. DOCKET NO.</b> <b>4590-410</b>		<b>U.S. APPLICATION NO.</b> <b>10/536696</b> <small>Not yet assigned</small>			
			<b>APPLICANT</b> <b>Arnaud GRISARD et al.</b>					
			<b>FILING DATE</b> <b>herewith</b>	<b>GROUP</b>				
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME		CLASS	SUBCLASS	FILING DATE	
<b>FOREIGN PATENT DOCUMENTS</b>								
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY		CLASS	SUBCLASS	Translation	
/J.R./	2 704 953	1994-11-10	FR				Yes	No
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
/J.R./	Angel M J et al: "Growth of alternating-oriented II-VI Regions of Quasi-Phase-Matched Nonlinear Optical Devices On Gaas Substrates" Applied Physics Letters, American Institute of Physics, NY June 6, 1994							
/J.R./	Becouarn L et al "Second harmonic generation of CO2laser using thick quasi-phase-matched GaAs layer grown by hydride vapour phase epitaxy" Electronics Letters, IEE Stevenage, GB vol. 34, No.25, December 10, 1998 pages 2409-2410							
/J.R./	Eyres L A et al: All Epitaxial Fabrication of Thick, Orientation-Patterned Gaas Films for Nonlinear Optical Frequency Conversion" Applied Physics Letters, American Institute of Physics, New York, August 13, 2001							
EXAMINER	/Joshel Rivera/			DATE CONSIDERED		11/18/2009		

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /J.R./